

D1
Cutter

these gases; a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas such as He or Ar; a temperature ranging from about 150 to about 600 degrees Celsius, a pressure ranging from about 50 millitorr to about 1 atmosphere (760 torr); and a process time ranging from about 50 to about 500 seconds. Again, one skilled in the art is aware that these parameters can be altered to achieve the same or a similar process.--

In the Claims:

Please cancel claim 77.

Please amend claims 43, 44, 76 and 78 as follows:

Snb 1
E
D

43. (Twice Amended) A method of passivating a multilayer conductive structure, comprising:

layering a first conductive material;

introducing said first conductive material to a material selected from the group consisting of diborane, phosphine, a carbon-silicon compound, HCL, and boron trichloride;

applying electromagnetic energy to the material introduced to the first conductive material; and

layering a second conductive material over said first conductive material.

44. (Twice Amended) The method in claim 43, wherein said step of applying electromagnetic energy to the material introduced to the first conductive material comprises directing ultraviolet light toward the material introduced to the first conductive material.

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Eg

76. (Twice Amended) A method of passivating a multilayer conductive structure, comprising:

layering a first conductive material;

introducing said first conductive material to a material selected from the group consisting of phosphine and a carbon-silicon compound;

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(cont'd)
applying electromagnetic energy to the material introduced to the
first conductive material; and
layering a second conductive material over said first conductive
material.

78. (Amended) A method of passivating a multilayer conductive structure,
comprising:

layering a first conductive material;
introducing the first conductive material to a material selected
from the group consisting of phosphine and a carbon-silicon compound; and
layering a second conductive material over the first conductive
material.

Please add new claims 79 and 80 as follows:

--79. (New) The method of claim 78 wherein the carbon-silicon compound is
selected from the group consisting of methylsilane CH_3SiH_3 , hexamethyldisilane $(\text{CH}_3)_3\text{Si}-\text{Si}(\text{CH}_3)_3$, and hexamethyldisilazane HMDS.

80. (New) The method of claim 43 wherein the carbon-silicon compound is
selected from the group consisting of methylsilane CH_3SiH_3 , hexamethyldisilane $(\text{CH}_3)_3\text{Si}-\text{Si}(\text{CH}_3)_3$, and hexamethyldisilazane HMDS.--

REMARKS

Claims 43, 44, and 76-78, along with newly added claims 79-80, are currently pending in the present patent application. In an Office Action mailed March 14, 2002, the Examiner objected to claims 43, 44, and 76-78 and rejected claim 44 under the second paragraph of 35 U.S.C. § 112 for several minor informalities in these claims. The claims have been amended to correct these minor informalities. The Examiner further rejected all pending claims under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 6,201,276 B1 to Agarwal *et al.*